

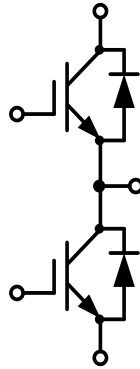
62mm Half Bridge IGBT Module

电气特性:

- 1200V 沟槽栅/场终止工艺
- 低开关损耗
- 正温度系数

典型应用:

- 逆变焊机
- 感应加热
- 高频开关应用
- 逆变器



$V_{CES} = 1200V$, $I_{C\ nom} = 200A$ / $I_{CRM} = 400A$

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
集电极-发射极电压 Collector-Emitter voltage	$T_{vj} = 25^{\circ}C$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 100^{\circ}C$, $T_{vj\ max} = 175^{\circ}C$	$I_{C\ nom}$	200	A
集电极重复峰值电流 Repetitive peak collector current	$t_p = 1\ ms$	I_{CRM}	400	A
栅极-发射极电压 Gate emitter voltage		V_{GE}	± 20	V

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-Emitter saturation voltage	$V_{GE} = 15V$, $I_C = 200A$ $V_{GE} = 15V$, $I_C = 200A$ $V_{GE} = 15V$, $I_C = 200A$	$T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 150^{\circ}C$	V_{CESat}	2.02 2.36 2.44	2.6	V
栅极-发射极阈值电压 Gate-Emitter threshold voltage	$I_C = 8mA$, $V_{GE} = V_{CE}$	$T_{vj} = 25^{\circ}C$	$V_{GE(th)}$	5.2	5.8	6.4
栅电荷 Gate charge	$V_{GE} = -15V \dots +15V$		Q_G	1.04		μC
内部栅极电阻 Internal gate resistor			R_{Gint}	3.70		Ω
输入电容 Input capacitance	$f = 100KHz$, $V_{CE} = 25\ V$, $V_{GE} = 0\ V$	$T_{vj} = 25^{\circ}C$	C_{ies}	11.69		nF

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反向传输电容 Reverse transfer capacitance			C_{res}		0.49		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V$	$T_{vj}=25^{\circ}C$	I_{CES}			2	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE}=0V, V_{GE}=20V$	$T_{vj}=25^{\circ}C$	I_{GES}			200	nA
开通延迟时间 Turn-on delay time	$I_C=200A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=6.8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	$t_{d\ on}$			170 173 179	ns
上升时间 Rise time	$I_C=200A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=6.8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	t_r			69 71 72	
关断延迟时间 Turn-off delay time	$I_C=200A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=6.8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	$t_{d\ off}$			324 377 395	
下降时间 Fall time	$I_C=200A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=6.8\Omega$ (电感负载) / (inductive load)	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	t_f			38 83 99	
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	$I_C=200A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=6.8\Omega$ $di/dt = 2100A/\mu s$ ($T_{vj} = 150^{\circ}C$) (电感负载) / (inductive load)	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	E_{on}			24.11 31.54 33.55	mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	$I_C=200A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=6.8\Omega$ $dv/dt = 5500V/\mu s$ ($T_{vj} = 150^{\circ}C$) (电感负载) / (inductive load)	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	E_{off}			7.86 11.23 12.73	
短路数据 SC data	$V_{GE}\leq 15V, V_{ce}=800V$ $V_{CEmax}=V_{CES}-L_{sCE}\cdot di/dt$ $t_p\leq 10\mu s, T_{vj}=150^{\circ}C$		I_{SC}			800	A
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	$^{\circ}C$

二极管，逆变器 / Diode, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj}=25^{\circ}C$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	200	A
正向重复峰值电流 Repetitive peak forward current	$t_p=1ms$	I_{FRM}	400	A
I^2t 值 I^2t -value	$t_p=10ms, \sin 180^{\circ}, T_j=125^{\circ}C$	I^2t	7000	A^2S

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
正向电压 Forward voltage	$I_F=200A, V_{GE}=0V$ $I_F=200A, V_{GE}=0V$ $I_F=200A, V_{GE}=0V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	V_F		2.16 2.11 2.02	2.8 V
反向恢复峰值电流 Peak reverse recovery current	$I_F=200A,$ $-di_F/dt=2100A/\mu s(T_{vj}=150^{\circ}C)$ $V_R=600V, V_{GE}=-15V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	I_{RM}		57 77 83	A
恢复电荷 Recovered charge	$I_F=200A,$ $-di_F/dt=2100A/\mu s(T_{vj}=150^{\circ}C)$ $V_R=600V, V_{GE}=-15V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	Q_r		9.99 22.24 24.81	μC
反向恢复损耗（每脉冲） Reverse recovered energy	$I_F=200A,$ $-di_F/dt=2100A/\mu s(T_{vj}=150^{\circ}C)$ $V_R=600V, V_{GE}=-15V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	E_{rec}		2.70 6.74 7.54	mJ
在开关状态下温度 Temperature under switching conditions			$T_{vj op}$	-40		150 $^{\circ}C$

模块 / Module

Parameter	Conditions	Symbol	Value			Unit
绝缘测试电压 Isolation test voltage	RMS, f=50Hz, t=1min	V_{ISOL}			4000	V
内部绝缘 Internal isolation					Al_2O_3	
储存温度 Storage temperature		T_{stg}	-40		125	$^{\circ}C$
模块安装的扭矩 Mounting torque for modul mounting		M	3.0		6.0	Nm
重量 Weight		W			324	g

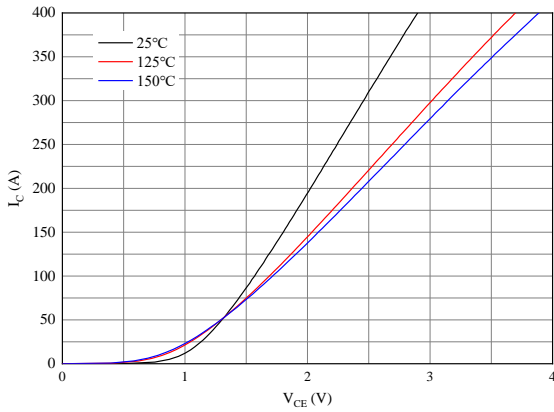


图 1. 典型输出特性 ($V_{GE}=15V$)
Figure 1. Typical output characteristics ($V_{GE}=15V$)

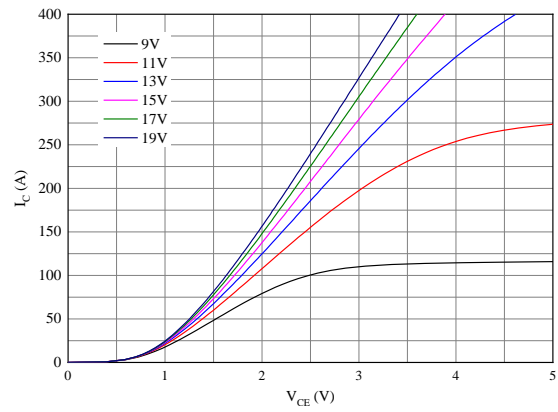


图 2. 典型输出特性 ($T_{vj}=150^{\circ}C$)
Figure 2. Typical output characteristics ($T_{vj}=150^{\circ}C$)

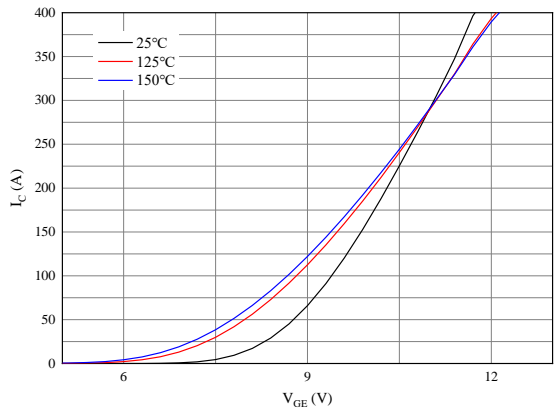


图 3. 典型传输特性 ($V_{CE}=20V$)
Figure 3. Typical transfer characteristic ($V_{CE}=20V$)

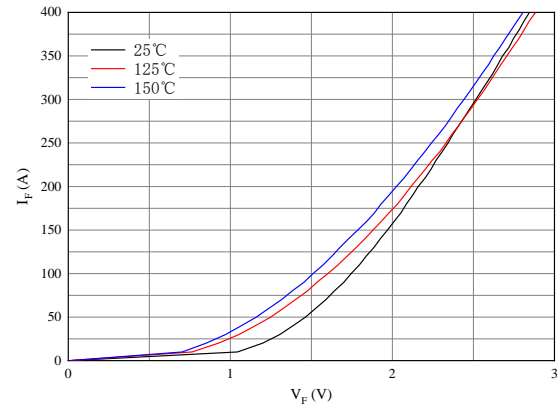


图 4. 正向偏压特性 二极管
Figure 4. Forward characteristic of Diode

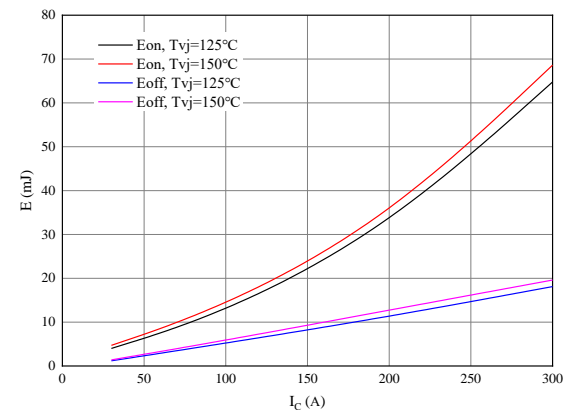


图 5. 开关损耗 逆变器
Figure 5. Switching losses of IGBT
 $V_{GE}=\pm 15V, R_{Gon}=6.8\Omega, R_{Goff}=6.8\Omega, V_{CE}=600V$

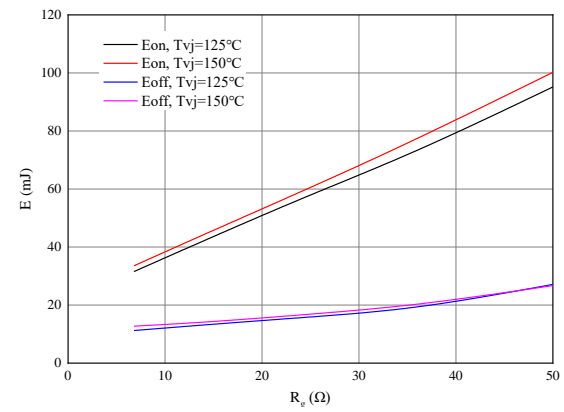


图 6. 开关损耗 逆变器
Figure 6. Switching losses of IGBT
 $V_{GE}=\pm 15V, I_C=200A, V_{CE}=600V$

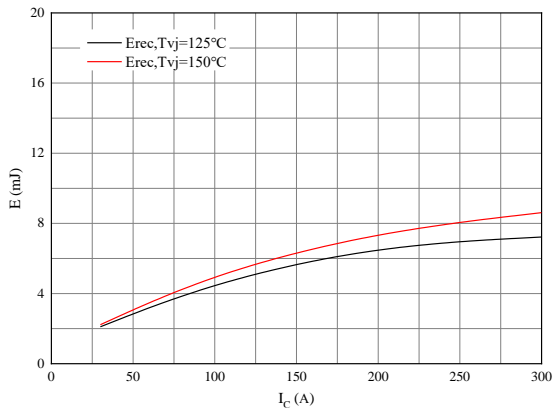


图 7. 开关损耗 二极管
 Figure 7. Switching losses of Diode
 R_{Gon}=6.8 Ω, V_{CE}=600V

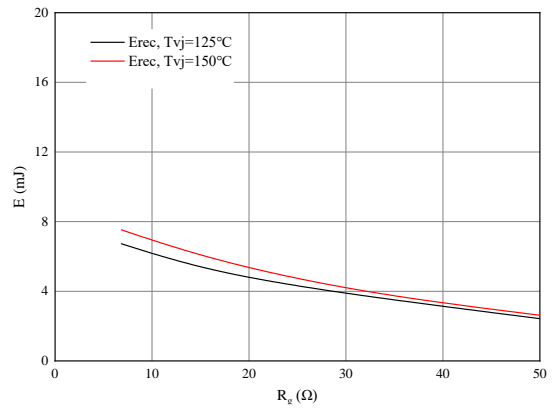


图 8. 开关损耗 二极管
 Figure 8. Switching losses of Diode
 I_F=200A, V_{CE}=600V

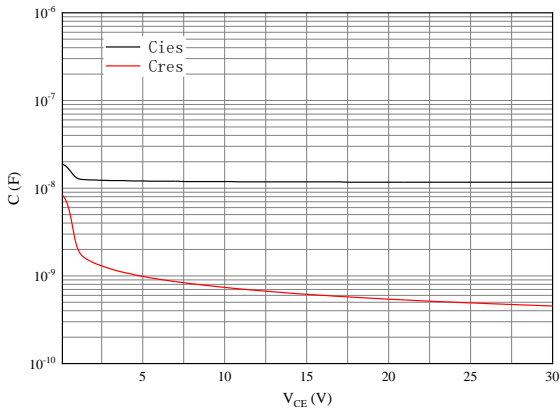
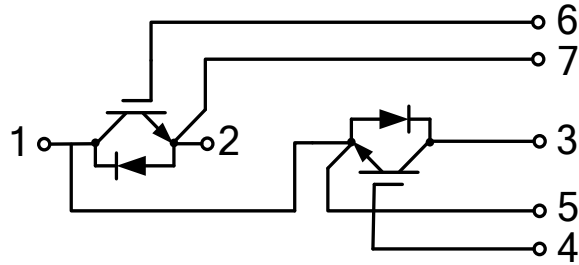
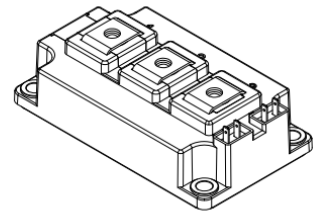
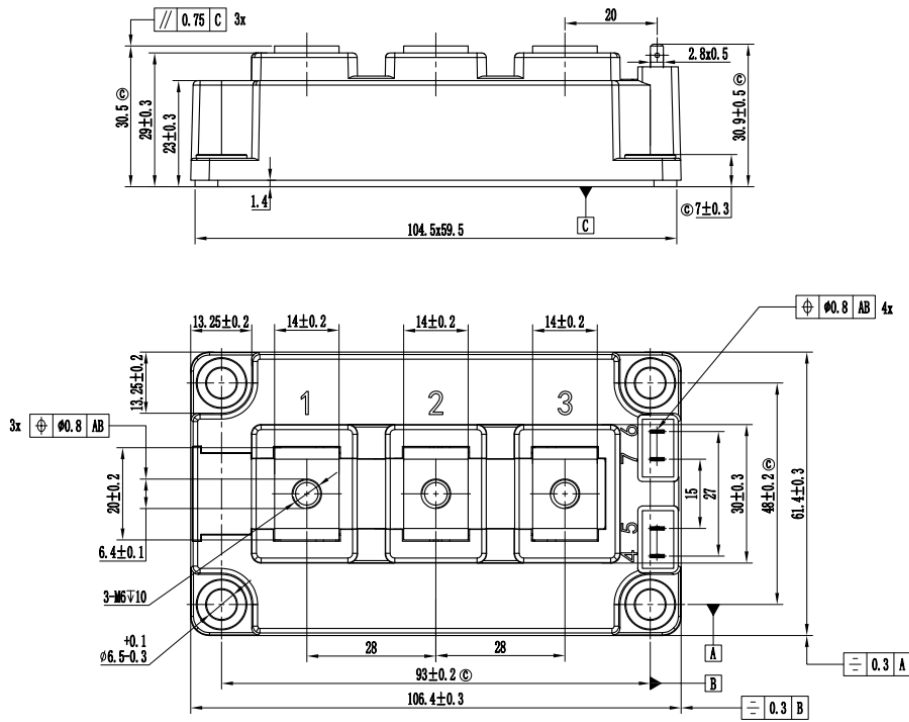


图 9. 电容特性
 Figure 9. Capacitance characteristic

接线图 / Circuit diagram



封装尺寸 / Package outlines



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2. 未标注公差按GB/T1804-m执行